Replaced by MHL19926N. There are no form, fit or function changes with this part replacement. N suffix added to part number to indicate transition to lead-free terminations.

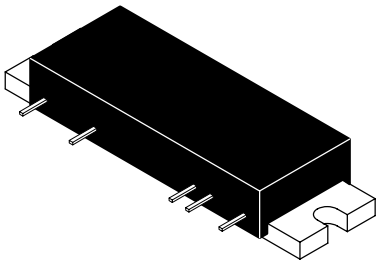
PCS Band
RF Linear LDMOS Amplifier

MHL19926

1930-1990 MHz, 10 W, 29.4 dB
RF LINEAR LDMOS AMPLIFIER

Designed for ultra-linear amplifier applications in 50 Ohm systems operating in the PCS frequency band. A silicon FET Class A design provides outstanding linearity and gain. In addition, the excellent group delay and phase linearity characteristics are ideal for digital modulation systems, such as TDMA, EDGE and CDMA.

- Third Order Intercept Point: 50 dBm Typ
- Power Gain: 29.4 dB Typ (@ f = 1960 MHz)
- Excellent Phase Linearity and Group Delay Characteristics
- Ideal for Feedforward Base Station Application



CASE 301AY-01, STYLE 1

ARCHIVE INFORMATION

Table 1. Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
DC Supply Voltage	V_{DD}	30	Vdc
RF Input Power	P_{in}	+17	dBm
Storage Temperature Range	T_{stg}	- 40 to +100	°C
Operating Case Temperature Range	T_C	- 20 to +100	°C

Table 2. Electrical Characteristics (T_C = +25°C; V_{DD} = 26 Vdc; 50 Ω System)

Characteristic		Symbol	Min	Typ	Max	Unit
Supply Current		I_{DD}	—	1	1.05	A
Power Gain	(f = 1960 MHz)	G_p	28.4	29.4	30.4	dB
Gain Flatness	(f = 1930-1990 MHz)	G_F	—	0.3	0.5	dB
Power Output @ 1 dB Compression	(f = 1960 MHz)	P1 dB	39	40	—	dBm
Input VSWR	(f = 1930-1990 MHz)	$VSWR_{in}$	—	1.2:1	1.5:1	
Third Order Intercept	(f1 =1957 MHz, f2=1962 MHz)	ITO	49.5	50	—	dBm
Noise Figure	(f = 1990 MHz)	NF	—	4.2	5	dB

NOTE - **CAUTION** - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.

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NOTES

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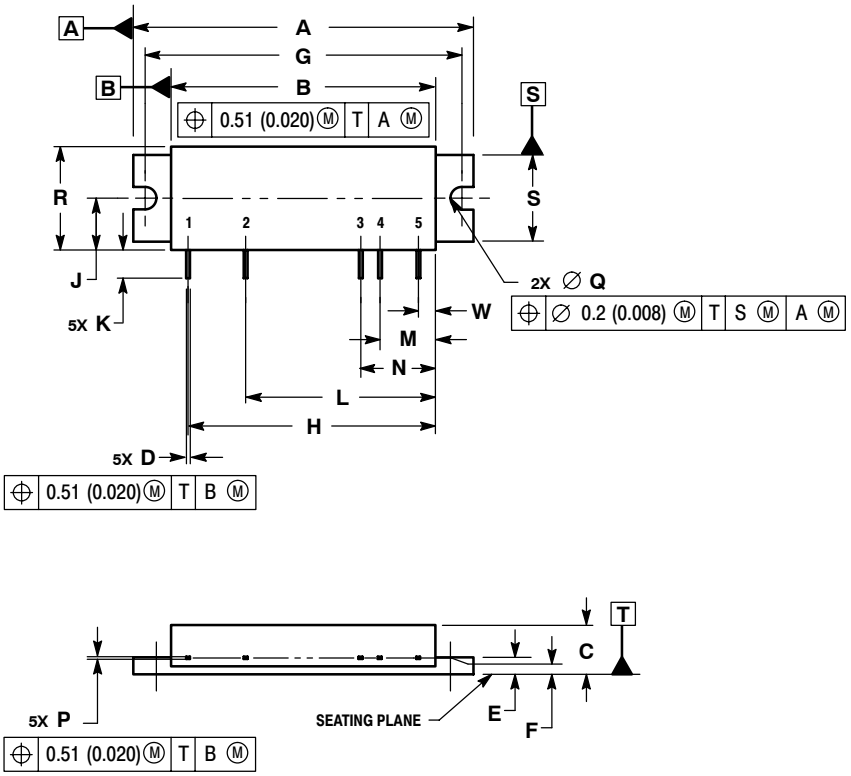
PACKAGE DIMENSIONS



NOTES:
1. CONTROLLING DIMENSION: MILLIMETER.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ANSI Y14.5M, 1982.
3. DIMENSION F TO CENTER LINE OF LEADS.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	44.7	45.21	1.760	1.780
B	34.8	35.31	1.370	1.390
C	6.22	6.73	0.245	0.265
D	0.43	0.58	0.017	0.023
E	2.03	2.54	0.080	0.100
F	2.18 BSC		0.086 BSC	
G	41.91 BSC		1.650 BSC	
H	32.77 BSC		1.290 BSC	
J	6.76	7.11	0.266	0.280
K	3.18	4.19	0.125	0.165
L	25.15 BSC		0.990 BSC	
M	7.37 BSC		0.290 BSC	
N	9.91 BSC		0.390 BSC	
P	0.2	0.33	0.008	0.013
Q	3	3.35	0.118	0.132
R	13.59	14.1	0.535	0.555
S	11.3	11.81	0.445	0.465
W	2.29 BSC		0.090 BSC	

STYLE 1:
PIN 1. RF INPUT
2. VDD1
3. VDD2
4. VDD3
5. RF OUTPUT
CASE: GROUND

CASE 301AY-01
ISSUE O

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How to Reach Us:

Home Page:
www.freescale.com

E-mail:
support@freescale.com

USA/Europe or Locations Not Listed:
Freescale Semiconductor
Technical Information Center, CH370
1300 N. Alma School Road
Chandler, Arizona 85224
+1-800-521-6274 or +1-480-768-2130
support@freescale.com

Europe, Middle East, and Africa:
Freescale Halbleiter Deutschland GmbH
Technical Information Center
Schatzbogen 7
81829 Muenchen, Germany
+44 1296 380 456 (English)
+46 8 52200080 (English)
+49 89 92103 559 (German)
+33 1 69 35 48 48 (French)
support@freescale.com

Japan:
Freescale Semiconductor Japan Ltd.
Headquarters
ARCO Tower 15F
1-8-1, Shimo-Meguro, Meguro-ku,
Tokyo 153-0064
Japan
0120 191014 or +81 3 5437 9125
support.japan@freescale.com

Asia/Pacific:
Freescale Semiconductor Hong Kong Ltd.
Technical Information Center
2 Dai King Street
Tai Po Industrial Estate
Tai Po, N.T., Hong Kong
+800 2666 8080
support.asia@freescale.com

For Literature Requests Only:
Freescale Semiconductor Literature Distribution Center
P.O. Box 5405
Denver, Colorado 80217
1-800-441-2447 or 303-675-2140
Fax: 303-675-2150
LDCForFreescaleSemiconductor@hibbertgroup.com

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